

August 2007

2.7V to 11V

## LMH6618

# 130 MHz, 1.25 mA Rail-to-Rail Input and Output Operational Amplifier with Shutdown

## **General Description**

The LMH6618 is a 130 MHz rail-to-rail input and output amplifier designed for ease of use in a wide range of applications requiring high speed, low supply current, low noise, and the ability to drive complex ADC and video loads. The operating voltage range extends from 2.7V to 11V and the supply current is typically 1.25 mA at 5V.

The amplifier's voltage feedback design topology provides balanced inputs and high open loop gain for ease of use and accuracy in applications such as active filter design. Offset voltage is typically 0.1 mV and settling time to 0.01% is 120 ns which combined with an 80 dBc SFDR at 1 MHz makes the part suitable for use as an input buffer for popular 10-bit and 12-bit mega-sample ADCs.

The input common mode range extends 200 mV beyond the supply rails. The output swings to within 270 mV of the supply rails for a 150 $\Omega$  load and 83 mV of the supply rail for a 1 k $\Omega$  load providing true single supply operation and maximum signal dynamic range on low power rails. The amplifier output will source and sink 35 mA and drive up to 15 pF loads without the need for external compensation.

The LMH6618 has an active low disable pin which reduces the supply current to  $72 \,\mu\text{A}$  and is offered in the space saving 6-Pin TSOT23 package. The LMH6618 is available with a  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$  extended industrial temperature grade.

### **Features**

Operating voltage range

 $\rm V_S = 5V, \, R_L = 1 \; k\Omega, \, T_A = 25^{\circ}C$  and  $\rm A_V = +1, \, unless$  otherwise specified.

_	operating remage range	2.7 7 10 117
	Supply current	1.25 mA
	Small signal bandwidth	130 MHz
	Slew rate	55 V/μs
	Settling time to 0.1%	90 ns
	Settling time to 0.01%	120 ns
	SFDR (f = 1 MHz, $A_V = +1$ , $V_{OUT} = 2 V_{Pl}$	80 dBc
	0.1 dB bandwidth $(A_V = +2)$	15 MHz
	Low voltage noise	10 nV/√Hz
	I <mark>ndustrial temperature</mark> grade	-40°C to +125°C

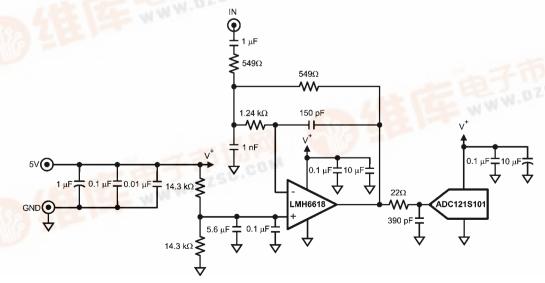
## **Applications**

- ADC driver
- DAC buffer
- Active filters
- High speed sensor amplifier

Rail-to-Rail input and output

- Current sense amplifier
- Portable video
- STB, TV video amplifier

## **Typical Application**



## **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

ESD Tolerance (Note 2) Human Body Model

For input pins only 2000V For all other pins 2000V

Machine Model 200V

Supply Voltage ( $V_S = V^+ - V^-$ ) 12V Junction Temperature (Note 3) 150°C max

## **Operating Ratings** (Note 1)

Supply Voltage ( $V_S = V^+ - V^-$ ) 2.7V to 11V Ambient Temperature Range (Note 3)  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ 

Package Thermal Resistance  $(\theta_{IA})$ 

6-Pin TSOT23 231°C/W

**+3V Electrical Characteristics** Unless otherwise specified, all limits are guaranteed for  $T_J = +25^{\circ}C$ ,  $V^+ = 3V$ ,  $V^- = 0V$ ,  $\overline{DISABLE} = 3V$ ,  $V_{CM} = V_O = V^+/2$ ,  $A_V = +1$  ( $R_F = 0\Omega$ ), otherwise  $R_F = 2$  k $\Omega$  for  $A_V \neq +1$ ,  $R_L = 1$  k $\Omega$  || 5 pF. **Boldface** Limits apply at temperature extremes. (Note 4)

Symbol	Symbol Parameter Condition		Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units	
Frequenc	∣ y Domain Response		[ (NOTE 0)	(Note 7)	(Note 6)		
SSBW	-3 dB Bandwidth Small Signal	$A_V = 1, R_L = 1 k\Omega, V_{OUT} = 0.2 V_{PP}$		120			
002	o az zanamam oman olgman	$A_V = 1$ , $H_L = 1$ $K\Omega$ , $V_{OUT} = 0.2$ $V_{PP}$		56		MHz	
GBW	Gain Bandwidth		55	71		MHz	
GBVV	dain bandwidin	$A_V = 10, R_F = 2 k\Omega, R_G = 221\Omega, R_L = 1 k\Omega,$ $V_{OUT} = 0.2 V_{PP}$	33	/ 1		IVII IZ	
LSBW	-3 dB Bandwidth Large Signal	$A_V = 1$ , $R_L = 1$ k $\Omega$ , $V_{OUT} = 2$ $V_{PP}$		13		MU	
		$A_V = 2$ , $R_L = 150\Omega$ , $V_{OUT} = 2 V_{PP}$		13		MHz	
Peak	Peaking	$A_V = 1, C_L = 5 pF$		1.5		dB	
0.1 dBBW	0.1 dB Bandwidth	$A_V = 2$ , $V_{OUT} = 0.5 V_{PP}$ , $R_F = R_G = 825\Omega$		15		MHz	
DG	Differential Gain	$A_V = +2$ , 4.43 MHz, 0.6V < $V_{OUT}$ < 2V, $R_L = 150\Omega$ to V+/2		0.1		%	
DP	Differential Phase	$A_V = +2$ , 4.43 MHz, 0.6V < $V_{OUT}$ < 2V, $R_L = 150\Omega$ to V+/2		0.1		deg	
Time Don	nain Response		•	•			
t <sub>r</sub> /t <sub>f</sub>	Rise & Fall Time	2V Step, A <sub>V</sub> = 1		36		ns	
SR	Slew Rate	2V Step, A <sub>V</sub> = 1	36	46		V/µs	
t <sub>s_0.1</sub>	0.1% Settling Time	2V Step, A <sub>V</sub> = -1					
t <sub>s_0.01</sub>	0.01% Settling Time	2V Step, A <sub>V</sub> = −1		120		ns	
	Distortion Performance		•	•			
SFDR	Spurious Free Dynamic Range	$f_C = 100 \text{ kHz}, V_{OUT} = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		100			
		$f_C = 1 \text{ MHz}, V_{OUT} = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		80		dBc	
		$f_C = 5 \text{ MHz}, V_{OUT} = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		58			
e <sub>n</sub>	Input Voltage Noise	f = 100 kHz		10		nV/√Hz	
i <sub>n</sub>	Input Current Noise	f = 100 kHz		1		pA∕√Hz	
Input, DC	Performance		1				
V <sub>OS</sub>	Input Offset Voltage	V <sub>CM</sub> = 0.5V (pnp active) V <sub>CM</sub> = 2.5V (npn active)		0.1	±0.6 ±1.0	mV	
TCV <sub>OS</sub>	Input Offset Voltage Average Drift	(Note 5)		0.8		μV/°C	
I <sub>B</sub>	Input Bias Current	V <sub>CM</sub> = 0.5V (pnp active)		-1.4	-2.6	_	
		V <sub>CM</sub> = 2.5V (npn active)		+1.0	+1.8	μA	
Io	Input Offset Current			0.01	±0.27	μΑ	
C <sub>IN</sub>	Input Capacitance			1.5		pF	
R <sub>IN</sub>	Input Resistance			8		ΜΩ	

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Symbol	Parameter	Condition	Min	Тур	Max	Units
			(Note 8)	(Note 7)	(Note 8)	
CMVR	Input Voltage Range	DC, CMRR ≥ 65 dB	-0.2		3.2	V
CMRR	Common Mode Rejection Ratio	V <sub>CM</sub> Stepped from -0.1V to 1.4V	78	96		dB
		V <sub>CM</sub> Stepped from 2.0V to 3.1V	81	107		uБ
A <sub>OL</sub>	Open Loop Gain	$R_L = 1 \text{ k}\Omega \text{ to V+/2}$		98		4D
		$R_L = 150\Omega$ to V+/2		82		dB
Output D	C Characteristics		•	•		
V <sub>O</sub>	Output Swing High	$R_L = 1 \text{ k}\Omega \text{ to V} + /2$	56	50		
	(Voltage from V+ Supply Rail)		62			
		R <sub>L</sub> =150Ω to V+/2	172	160		
			198			
	Output Swing Low	$R_L = 1 \text{ k}\Omega \text{ to V} + /2$		60	66	mV
	(Voltage from V- Supply Rail)				74	111 V
		$R_L = 150\Omega$ to V+/2		170	184	
		_			217	
		$R_1 = 150\Omega$ to V-		29	39	
					43	
I <sub>OUT</sub>	Linear Output Current	V <sub>OUT</sub> = V+/2 (Note 6)	±25	±35		mA
R <sub>O</sub>	Output Resistance	f = 1 MHz		0.17		Ω
Enable Pi	n Operation					
	Enable High Voltage Threshold	Enabled	2.0			V
	Enable Pin High Current	V <sub>DISABLE</sub> = 3V		0.04		μΑ
	Enable Low Voltage Threshold	Disabled			1.0	V
	Enable Pin Low Current	$V_{\overline{\text{DISABLE}}} = 0V$		1		μΑ
T <sub>on</sub>	Turn-On Time			25		ns
T <sub>off</sub>	Turn-Off Time			90		ns
Power Su	pply Performance				-	
PSRR	Power Supply Rejection Ratio	DC, $V_{CM} = 0.5V$ , $V_{S} = 2.7V$ to 11V	84	104		dB
I <sub>s</sub>	Supply Current	R <sub>L</sub> = ∞		1.2	1.5	m A
					1.7	mA
I <sub>SD</sub>	Disable Shutdown Current	DISABLE = 0V		59	85	μA

**+5V Electrical Characteristics** Unless otherwise specified, all limits are guaranteed for  $T_J = +25^{\circ}C$ ,  $V^+ = 5V$ ,  $V^- = 0V$ ,  $\overline{DISABLE} = 5V$ ,  $V_{CM} = V_O = V^+/2$ ,  $A_V = +1$  ( $R_F = 0\Omega$ ), otherwise  $R_F = 2$  k $\Omega$  for  $A_V \neq +1$ ,  $R_L = 1$  k $\Omega$  || 5 pF. **Boldface** Limits apply at temperature extremes.

Symbol	Parameter	Condition	Min	Тур	Max	Units
			(Note 8)	(Note 7)	(Note 8)	
Frequenc	y Domain Response					
SSBW	-3 dB Bandwidth Small Signal	$A_V = 1, R_L = 1 \text{ k}\Omega, V_{OUT} = 0.2 \text{ V}_{PP}$		130		MHz
		$A_V = 2, -1, R_L = 1 k\Omega, V_{OUT} = 0.2 V_{PP}$		53		IVIITZ
GBW	Gain Bandwidth	$A_V = 10, R_F = 2 k\Omega, R_G = 221\Omega, R_L = 1 k\Omega,$	54	64		MHz
		$V_{OUT} = 0.2 V_{PP}$				
LSBW	-3 dB Bandwidth Large Signal	$A_V = 1$ , $R_L = 1$ k $\Omega$ , $V_{OUT} = 2$ $V_{PP}$		15		MHz
		$A_V = 2$ , $R_L = 150\Omega$ , $V_{OUT} = 2 V_{PP}$		15		IVII IZ
Peak	Peaking	$A_V = 1, C_L = 5 pF$		0.5		dB
0.1	0.1 dB Bandwidth	$A_V = 2$ , $V_{OUT} = 0.5 V_{PP}$ ,		15		MHz
dBBW		$R_F = R_G = 1 \text{ k}\Omega$				
DG	Differential Gain	$A_V = +2, 4.43 \text{ MHz}, 0.6V < V_{OUT} < 2V,$		0.1		%
		$R_L = 150\Omega$ to V+/2				

Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units	
DP	Differential Phase	A <sub>V</sub> = +2, 4.43 MHz, 0.6V < V <sub>OUT</sub> < 2V,	( 2.2.2)	0.1	( 222 2)	deg	
		$R_{L} = 150\Omega$ to V+/2					
Time Don	nain Response				1	1	
t <sub>r</sub> /t <sub>f</sub>	Rise & Fall Time	2V Step, A <sub>V</sub> = 1		30		ns	
SR	Slew Rate	2V Step, A <sub>V</sub> = 1	44	55		V/µs	
t <sub>s_0.1</sub>	0.1% Settling Time	2V Step, A <sub>V</sub> = −1		90		ns	
t <sub>s_0.01</sub>	0.01% Settling Time	2V Step, A <sub>V</sub> = −1		120		113	
Distortion	and Noise Performance						
SFDR	Spurious Free Dynamic Range	$f_C = 100 \text{ kHz}, V_{OUT} = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		100			
		$f_C = 1 \text{ MHz}, V_{OUT} = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		80		dBc	
		$f_C = 5 \text{ MHz}, V_O = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		58			
e <sub>n</sub>	Input Voltage Noise	f = 100 kHz		10		nV/√H:	
i <sub>n</sub>	Input Current Noise	f = 100 kHz		1		p <b>A</b> /√H:	
	Performance					pA/411/	
V <sub>OS</sub>	Input Offset Voltage	V <sub>CM</sub> = 0.5V (pnp active)	1	0.1	±0.6		
<b>v</b> os	Imput Offset Voltage	V <sub>CM</sub> = 4.5V (pnp active)		0.1	±1.0	mV	
TCV <sub>OS</sub>	Input Offset Voltage Average	(Note 5)		0.8		μV/°C	
. 0 . 08	Drift	(1000)		0.0		μ.,, σ	
I <sub>B</sub>	Input Bias Current	V <sub>CM</sub> = 0.5V (pnp active)		-1.5	-2.4	_	
_		V <sub>CM</sub> = 4.5V (npn active)		+1.0	+1.9	μA	
I <sub>o</sub>	Input Offset Current			0.01	±0.26	μA	
C <sub>IN</sub>	Input Capacitance			1.5		pF	
R <sub>IN</sub>	Input Resistance			8		MΩ	
CMVR	Input Voltage Range	DC, CMRR ≥ 65 dB	-0.2		5.2	V	
CMRR	Common Mode Rejection Ratio	V <sub>CM</sub> Stepped from –0.1V to 3.4V	81	98			
• • • • • • • • • • • • • • • • • • • •	Common mode risjection riams	V <sub>CM</sub> Stepped from 4.0V to 5.1V	84	108		dB	
AOL	Open Loop Gain	$R_L = 1 \text{ k}\Omega \text{ to V}^{+/2}$	<del>  •</del>	100			
	open zeep dam.			83		dB	
Output D	C Characteristics	$R_{L} = 150\Omega \text{ to V} + /2$		00			
	C Characteristics Output Swing High	D 11/0 to 1/1/0	73	60			
<b>v</b> O	(Voltage from V+ Supply Rail)	$R_L = 1 \text{ k}\Omega \text{ to V} + /2$	82				
		$R_1 = 150\Omega$ to V+/2	255	230			
		1.001110 1 /2	295				
	Output Swing Low	$R_L = 1 \text{ k}\Omega \text{ to V+/2}$		75	83	mV	
	(Voltage from V- Supply Rail)				96		
		$R_L = 150\Omega$ to V+/2		250	270		
					321		
		$R_L = 150\Omega$ to V-		32	43 <b>45</b>		
I <sub>OUT</sub>	Linear Output Current	V <sub>OUT</sub> = V+/2 (Note 6)	±25	±35	75	mA	
R <sub>O</sub>	Output Resistance	f = 1 MHz	120	0.17		Ω	
	n Operation	1 - 1 101112		0.17		52	
LIIADIE P	Enable High Voltage Threshold	Enabled	3.0			V	
	Enable Pin High Current	V <sub>DISABLE</sub> = 5V	0.0	1.2		μA	
	Enable Low Voltage Threshold	Disabled		1.2	2.0	V	
	Enable Pin Low Current	V <sub>DISABLE</sub> = 0V		2.5	2.0	μA	
т	Turn-On Time	V DISABLE - VV		2.5		ns	
T <sub>on</sub>							
T <sub>off</sub>	Turn-Off Time			90		ns	

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Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units			
Power Supply Performance									
PSRR	Power Supply Rejection Ratio	DC, $V_{CM} = 0.5V$ , $V_{S} = 2.7V$ to 11V	84	104		dB			
I <sub>s</sub>	Supply Current	$R_1 = \infty$		1.25	1.5	mA			
		-			1.7	IIIA			
I <sub>SD</sub>	Disable Shutdown Current	DISABLE = 0V		72	105	μA			

**±5V Electrical Characteristics** Unless otherwise specified, all limits are guaranteed for  $T_J = +25^{\circ}C$ ,  $V^+ = 5V$ ,  $V^- = -5V$ ,  $\overline{DISABLE} = 5V$ ,  $V_{CM} = V_O = 0V$ ,  $A_V = +1$  ( $R_F = 0\Omega$ ), otherwise  $R_F = 2$  k $\Omega$  for  $A_V \neq +1$ ,  $R_L = 1$  k $\Omega$  || 5 pF. **Boldface** Limits apply at temperature extremes.

Symbol	Parameter	Parameter Condition		Typ (Note 7)	Max (Note 8)	Units
Frequenc	y Domain Response	1	, ,	,	,	
SSBW	-3 dB Bandwidth Small Signal	$A_V = 1, R_L = 1 \text{ k}\Omega, V_{OUT} = 0.2 \text{ V}_{PP}$		140		
		$A_V = 2, -1, R_L = 1 \text{ k}\Omega, V_{OUT} = 0.2 V_{PP}$		53		MHz
GBW	Gain Bandwidth	$A_V = 10, R_F = 2 k\Omega, R_G = 221\Omega, R_L = 1 k\Omega,$	54	65		MHz
		$V_{OUT} = 0.2 V_{PP}$				
LSBW	-3 dB Bandwidth Large Signal	$A_V = 1$ , $R_L = 1$ k $\Omega$ , $V_{OUT} = 2$ $V_{PP}$		16		N 41 1-
		$A_V = 2$ , $R_L = 150\Omega$ , $V_{OUT} = 2 V_{PP}$		15		MHz
Peak	Peaking	$A_V = 1, C_L = 5 pF$		0.05		dB
0.1	0.1 dB Bandwidth	$A_V = 2$ , $V_{OUT} = 0.5 V_{PP}$ ,		15		MHz
dBBW		$R_F = R_G = 1.21 \text{ k}\Omega$				
DG	Differential Gain	$A_V = +2, 4.43 \text{ MHz}, 0.6V < V_{OUT} < 2V,$		0.1		%
		$R_L = 150\Omega$ to V+/2				
DP	Differential Phase	$A_V = +2, 4.43 \text{ MHz}, 0.6V < V_{OUT} < 2V,$		0.1		deg
		$R_L = 150\Omega$ to V+/2				
	nain Response	1	1			
t <sub>r</sub> /t <sub>f</sub>	Rise & Fall Time	2V Step, A <sub>V</sub> = 1		30		ns
SR	Slew Rate	2V Step, A <sub>V</sub> = 1	45	57		V/µs
t <sub>s_0.1</sub>	0.1% Settling Time 2V Step, $A_V = -1$			90		ns
t <sub>s_0.01</sub>	0.01% Settling Time	2V Step, A <sub>V</sub> = −1		120		
	d Distortion Performance	1	1			
SFDR	Spurious Free Dynamic Range	$f_C = 100 \text{ kHz}, V_{OUT} = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		100		
		$f_C = 1 \text{ MHz}, V_{OUT} = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		80		dBc
		$f_C = 5 \text{ MHz}, V_{OUT} = 2 V_{PP}, R_L = 1 \text{ k}\Omega$		58		
e <sub>n</sub>	Input Voltage Noise	f = 100 kHz		10		nV/√Hz
i <sub>n</sub>	Input Current Noise	f = 100 kHz		1		pA/√Hz
Input DC	Performance					
V <sub>os</sub>	Input Offset Voltage	V <sub>CM</sub> = -4.5V (pnp active)		0.1	±0.6	mV
		V <sub>CM</sub> = 4.5V (npn active)			±1.0	IIIV
TCV <sub>OS</sub>	Input Offset Voltage Average Drift	(Note 5)		0.9		μV/°C
I <sub>B</sub>	Input Bias Current	V <sub>CM</sub> = -4.5V (pnp active)		-1.5	-2.4	
		V <sub>CM</sub> = 4.5V (npn active)		+1.0	+1.9	μA
I <sub>O</sub>	Input Offset Current			0.01	±0.26	μΑ
C <sub>IN</sub>	Input Capacitance			1.5		pF
R <sub>IN</sub>	Input Resistance			8		МΩ
CMVR	Input Voltage Range	DC, CMRR ≥ 65 dB	-5.2		5.2	V

Symbol	Parameter	Condition	Min	Тур	Max	Units
			(Note 8)	(Note 7)	(Note 8)	
CMRR	Common Mode Rejection Ratio	V <sub>CM</sub> Stepped from –5.1V to 3.4V	84	100		dB
		V <sub>CM</sub> Stepped from 4.0V to 5.1V	83	108		
$A_{OL}$	Open Loop Gain	$R_L = 1 \text{ k}\Omega \text{ to V} + /2$		95		dB
		R <sub>L</sub> = 150Ω to V+/2		84		иь
Output D	C Characteristics		•		•	
v <sub>o</sub>	Output Swing High	$R_L = 1 \text{ k}\Omega \text{ to GND}$	111	100		
	(Voltage from V+ Supply Rail)	_	126			
		$R_L = 150\Omega$ to GND	457	430		
			526			
	Output Swing Low	$R_L = 1 \text{ k}\Omega \text{ to GND}$		110	121	mV
	(Voltage from V- Supply Rail)				136	111.0
		$R_L = 150\Omega$ to GND		440	474	
					559	
		$R_L = 150\Omega$ to V-		35	51	
					52	
I <sub>OUT</sub>	Linear Output Current	V <sub>OUT</sub> = V+/2 (Note 6)	±25	±35		mA
R <sub>O</sub>	Output Resistance	f = 1 MHz		0.17		Ω
Enable P	in Operation					
	Enable High Voltage Threshold	Enabled	5.5			V
	Enable Pin High Current	$V_{\overline{\text{DISABLE}}} = +5V$		16		μΑ
	Enable Low Voltage Threshold	Disabled			4.5	V
	Enable Pin Low Current	$V_{\overline{\text{DISABLE}}} = -5V$		17		μΑ
$T_{on}$	Turn-On Time			25		ns
$T_{off}$	Turn-Off Time			90		ns
Power Su	ipply Performance					
PSRR	Power Supply Rejection Ratio	DC, $V_{CM} = -4.5V$ , $V_{S} = 2.7V$ to 11V	84	104		dB
I <sub>S</sub>	Supply Current	$R_L = \infty$		1.35	1.6	mΛ
		_			1.9	mA
I <sub>SD</sub>	Disable Shutdown Current	DISABLE = -5V		103	140	μΑ

**Note 1:** Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.

Note 2: Human Body Model, applicable std. MIL-STD-883, Method 3015.7. Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC) Field-Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).

Note 3: The maximum power dissipation is a function of  $T_{J(MAX)}$ ,  $\theta_{JA}$ . The maximum allowable power dissipation at any ambient temperature is  $P_D = (T_{J(MAX)} - T_A) / \theta_{JA}$ . All numbers apply for packages soldered directly onto a PC Board.

Note 4: Boldface limits apply to temperature range of -40°C to 125°C

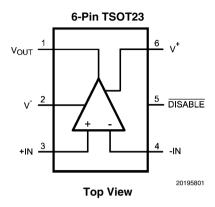
Note 5: Voltage average drift is determined by dividing the change in  $V_{OS}$  by temperature change.

Note 6: Do not short circuit the output. Continuous source or sink currents larger than the I<sub>OUT</sub> typical are not recommended as it may damage the part.

Note 7: Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.

Note 8: Limits are 100% production tested at 25°C. Limits over the operating temperature range are guaranteed through correlations using the Statistical Quality Control (SQC) method.

## **Connection Diagram**

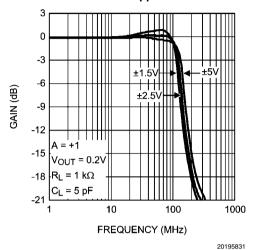


## **Ordering Information**

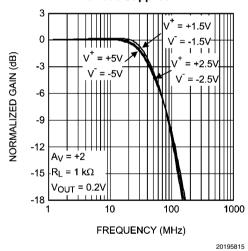
Package	Package Part Number Package Marking		Transport Media	NSC Drawing
6 Din TOOTOO	LMH6618MK	AE4A	1k Units Tape and Reel	MK06A
6-Pin TSOT23	LMH6618MKX	AE4A	3k Units Tape and Reel	IVIKUBA

## **Typical Performance Characteristics** At $T_J = 25^{\circ}C$ , $A_V = +1$ ( $R_F = 0\Omega$ ), otherwise $R_F = 2 \text{ k}\Omega$ for $A_V \neq +1$ , unless otherwise specified.

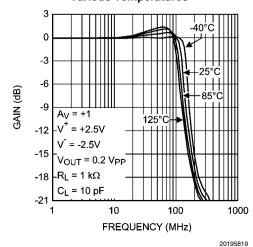
#### Closed Loop Frequency Response for Various Supplies



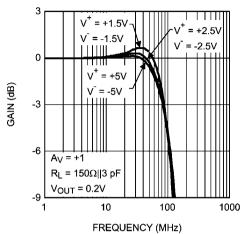
#### Closed Loop Frequency Response for Various Supplies



#### Closed Loop Frequency Response for Various Temperatures

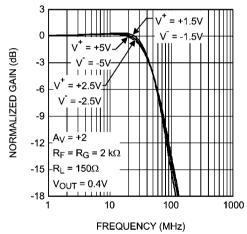


#### Closed Loop Frequency Response for Various Supplies



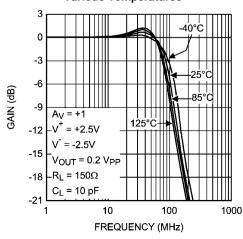
20195816

#### Closed Loop Frequency Response for Various Supplies



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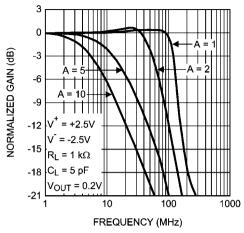
#### Closed Loop Frequency Response for Various Temperatures



20195820

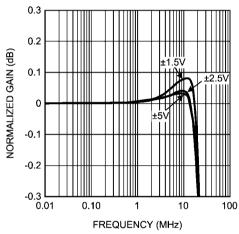
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## Closed Loop Gain vs. Frequency for Various Gains



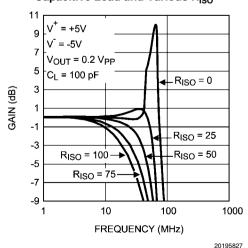
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#### ±0.1 dB Gain Flatness for Various Supplies

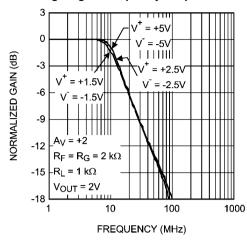


20195832

## Small Signal Frequency Response with Capacitive Load and Various R<sub>ISO</sub>

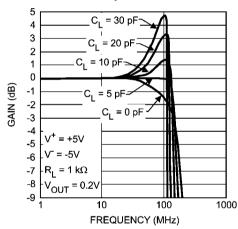


**Large Signal Frequency Response** 



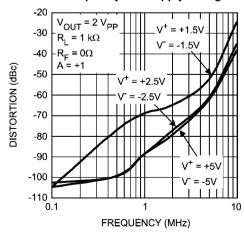
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#### Small Signal Frequency Response with Various Capacitive Load

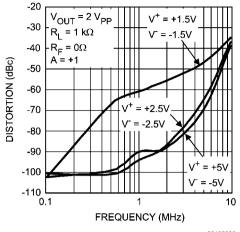


20195826

#### HD2 vs. Frequency and Supply Voltage

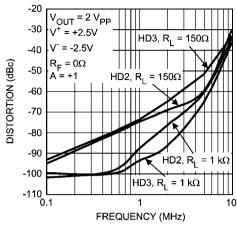


#### HD3 vs. Frequency and Supply Voltage



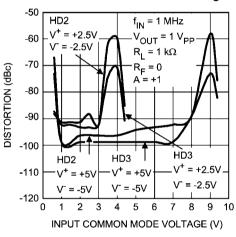
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## HD2 and HD3 vs. Frequency and Load



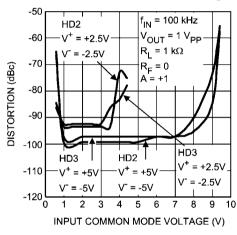
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#### HD2 and HD3 vs. Common Mode Voltage



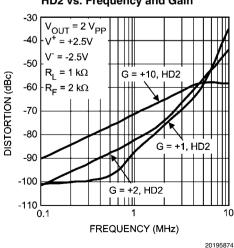
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HD2 and HD3 vs. Common Mode Voltage

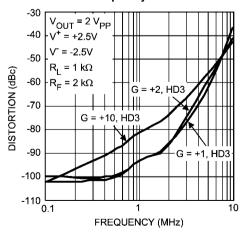


20195873

#### HD2 vs. Frequency and Gain



HD3 vs. Frequency and Gain



#### Open Loop Gain/Phase 120 120 100 100 PHASE 80 80 GAIN GAIN (dB) 60 40 20 20 -2.5V 0 -20 └ 1k 10k 100k 1M 10M 1G FREQUENCY (Hz) 20195833

#### -40 = -2.5V $R_L = 1 k\Omega$ -50 5 MHz HD2 (dBc) -60 -70 1 MHz -80 500 kHz -90 100 kHz -100 0 V<sub>OUT</sub> (V<sub>PP</sub>)

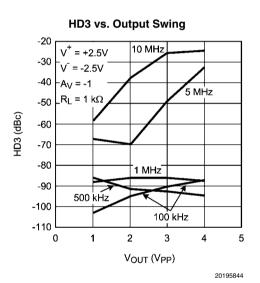
HD2 vs. Output Swing

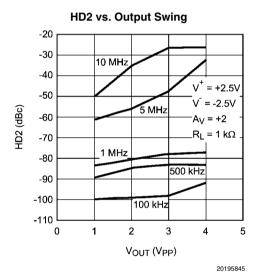
= +2.5V

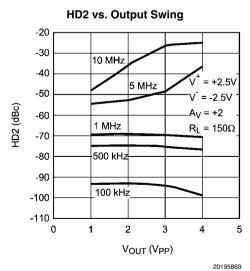
-30

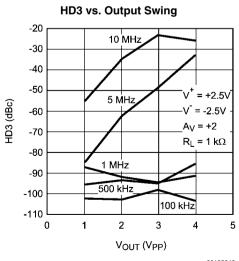
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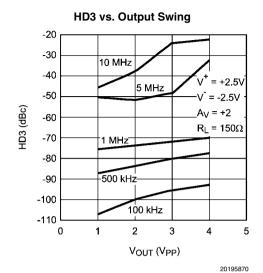
10 MHz

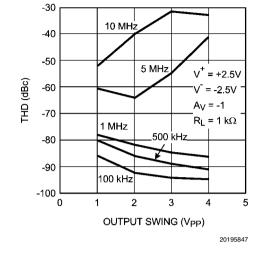




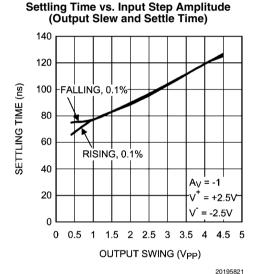


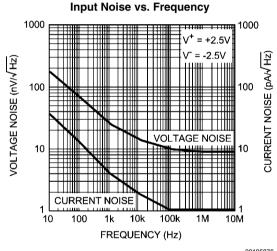




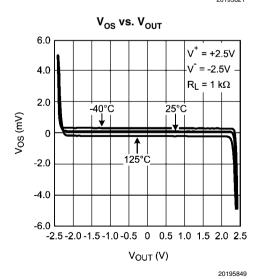


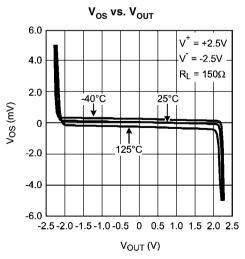
THD vs. Output Swing

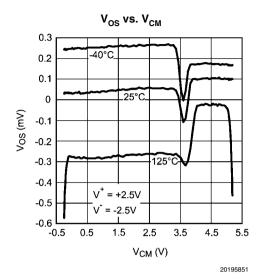


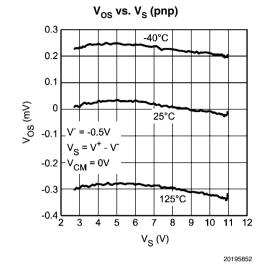


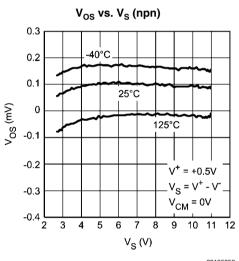
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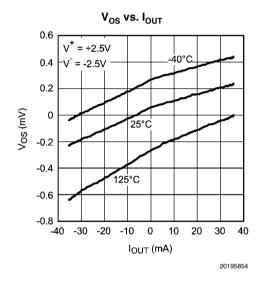


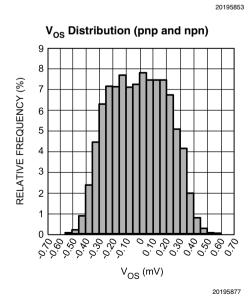


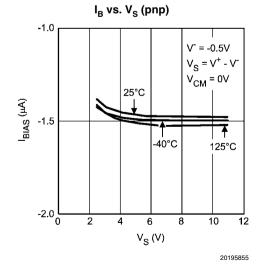


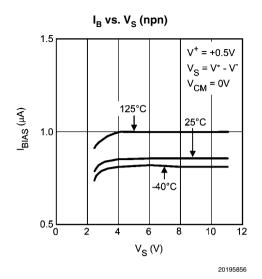


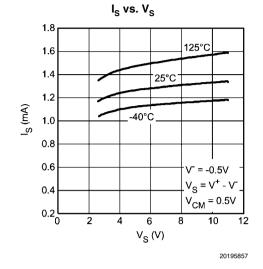












V<sub>OUT</sub> vs. V<sub>S</sub>

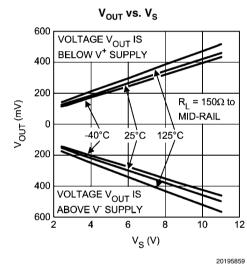
150
VOLTAGE V<sub>OUT</sub> IS
BELOW V<sup>+</sup> SUPPLY

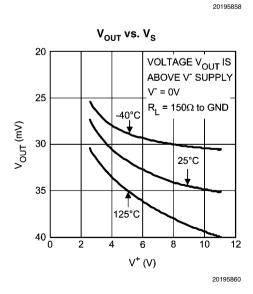
50
40°C 25°C 125°C

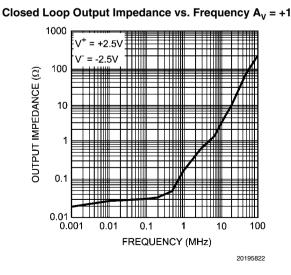
VOLTAGE V<sub>OUT</sub> IS
ABOVE V SUPPLY

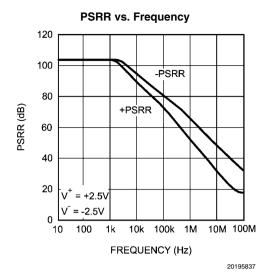
4 6 8 10 12

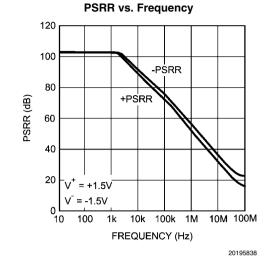
V<sub>S</sub> (V)



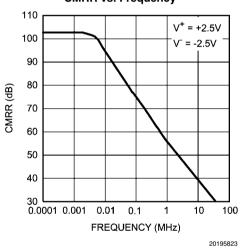


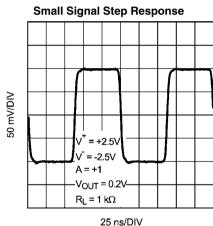




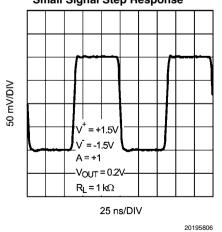


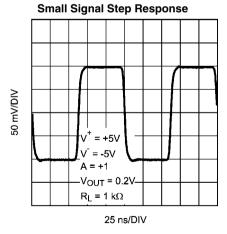
CMRR vs. Frequency





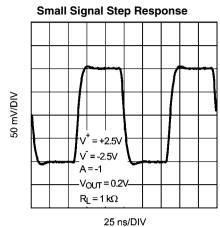
Small Signal Step Response



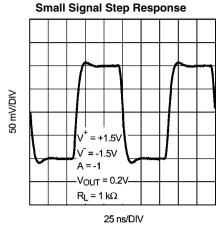


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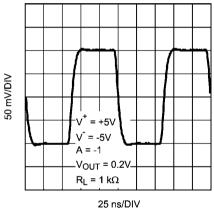






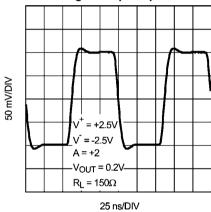
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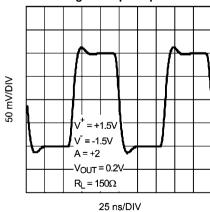
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#### **Small Signal Step Response**



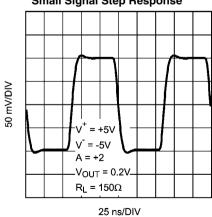
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#### **Small Signal Step Response**



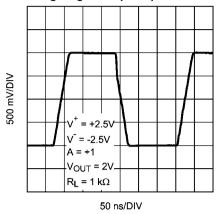
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#### **Small Signal Step Response**



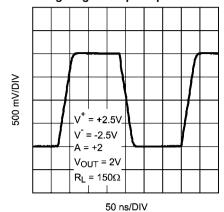
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### Large Signal Step Response



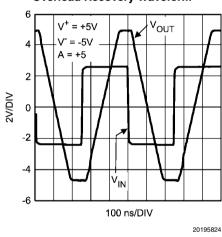
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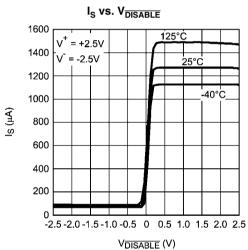
### Large Signal Step Response



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#### **Overload Recovery Waveform**





## **Application Information**

The LMH6618 is based on National Semiconductor's proprietary VIP10 dielectrically isolated bipolar process. This device family architecture features the following:

- Complimentary bipolar devices with exceptionally high f<sub>t</sub> (~8GHz) even under low supply voltage (2.7V) and low bias current.
- Common emitter push-push output stage. This architecture allows the output to reach within millivolts of either supply rail.
- Consistent performance from any supply voltage (2.7V -11V) with little variation with supply voltage for the most important specifications (e.g. BW, SR, I<sub>OUT</sub>.)
- Significant power saving compared to competitive devices on the market with similar performance.

With 3V supplies and a common mode input voltage range that extends beyond either supply rail, the LMH6618 is well suited to many low voltage/low power applications. Even with 3V supplies, the -3 dB BW (at  $A_V = +1$ ) is typically 120 MHz.

The LMH6618 is designed to avoid output phase reversal. With input over-drive, the output is kept near the supply rail (or as close to it as mandated by the closed loop gain setting and the input voltage). *Figure 1* shows the input and output voltage when the input voltage significantly exceeds the supply voltages.

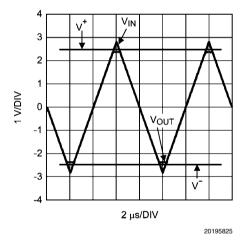


FIGURE 1. Input and Output Shown with CMVR Exceeded

If the input voltage range is exceeded by more than a diode drop beyond either rail, the internal ESD protection diodes will start to conduct. The current flow in these ESD diodes should be externally limited.

 $\frac{\mbox{The LMH6618 can be shutdown by connecting the }}{\mbox{DISABLE}} \mbox{ pin to a voltage 0.5V below the supply midpoint}}$ 

which will reduce the supply current to typically less than 100  $\mu$ A. The  $\overline{DISABLE}$  pin is "active low" and should be connected through a resistor to V+ for normal operation. Shutdown is guaranteed when the  $\overline{DISABLE}$  pin is 0.5V below the supply midpoint at any operating supply voltage and temperature.

In the shutdown mode, essentially all internal device biasing is turned off in order to minimize supply current flow and the output goes into high impedance mode. During shutdown, the input stage has an equivalent circuit as shown in *Figure 2*.

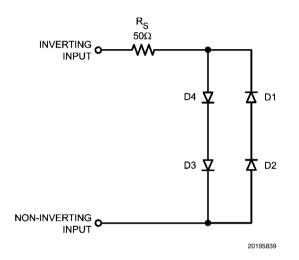


FIGURE 2. Input Equivalent Circuit During Shutdown

When the LMH6618 is shutdown, there may be current flow through the internal diodes shown, caused by input potential, if present. This current may flow through the external feedback resistor and result in an apparent output signal. In most shutdown applications the presence of this output is inconsequential. However, if the output is "forced" by another device, the other device will need to conduct the current described in order to maintain the output potential.

To keep the output at or near ground during shutdown when there is no other device to hold the output low, a switch using a transistor can be used to shunt the output to ground.

#### SINGLE CHANNEL ADC DRIVER

The low noise and wide bandwidth make the LMH6618 an excellent choice for driving a 12-bit ADC. *Figure 3* shows the schematic of the LMH6618 driving an ADC121S101. The ADC121S101 is a single channel 12-bit ADC. The LMH6618 is set up in a 2nd order multiple-feedback configuration with a gain of –1. The –3 db point is at 500 kHz and the –0.01 dB point is at 100 kHz. *Table 1* shows the performance data of the LMH6618 and the ADC121S101.

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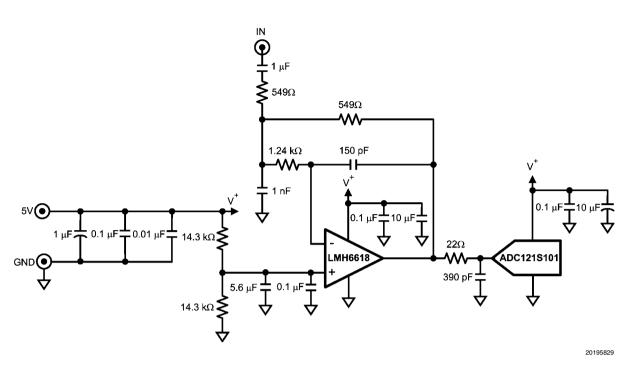


FIGURE 3. LMH6618 Driving an ADC121S101

TABLE 1. Performance Data for the LMH6618 Driving an ADC121S101

Parameter	Measured Value
Signal Frequency	100 kHz
Signal Amplitude	4.5V
SINAD	71.5 dB
SNR	71.87 dB
THD	-82.4 dB
SFDR	90.97 dB
ENOB	11.6 bits

When the op amp and the ADC are using the same supply, it is important that both devices are well bypassed. A 0.1  $\mu$ F ceramic capacitor and a 10  $\mu$ F tantalum capacitor should be located as close as possible to each supply pin. A sample

layout is shown in Figure 4. The 0.1  $\mu$ F capacitors (C13 and C6) and the 10  $\mu$ F capacitors (C11 and C5) are located very close to the supply pins of the LMH6618 and the AD-C121S101.

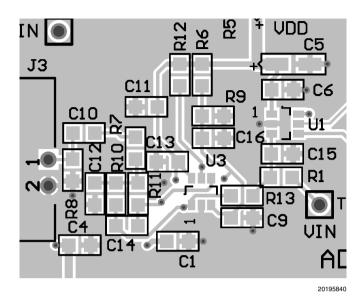


FIGURE 4. LMH6618 and ADC121S101 Layout

#### **DIFFERENTIAL ADC DRIVER**

The circuit in *Figure 3* can be used to drive both inputs of a differential ADC. *Figure 5* shows the LMH6618 driving an AD-

C121S705. The ADC121S705 is a fully differential 12-bit ADC. Performance with this circuit is similar to the circuit in *Figure 3*.

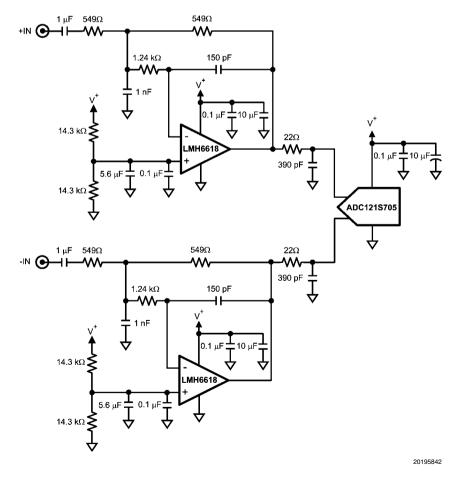


FIGURE 5. LMH6618 Driving an ADC121S705

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#### DC LEVEL SHIFTING

Often a signal must be both amplified and level shifted while using a single supply for the op amp. The circuit in *Figure 6* can do both of these tasks. The procedure for specifying the resistor values is as follows.

- 1. Determine the input voltage.
- 2. Calculate the input voltage midpoint,  $V_{INMID} = V_{INMIN} + (V_{INMAX} V_{INMIN})/2$ .
- 3. Determine the output voltage needed.
- Calculate the output voltage midpoint, V<sub>OUTMID</sub> = V<sub>OUTMIN</sub> + (V<sub>OUTMAX</sub> V<sub>OUTMIN</sub>)/2.
- 5. Calculate the gain needed, gain =  $(V_{OUTMAX} V_{OUTMIN})/(V_{INMAX} V_{INMIN})$
- 6. Calculate the amount the voltage needs to be shifted from input to output,  $\Delta V_{OUT} = V_{OUTMID} gain \times V_{INMID}$ .
- 7. Set the supply voltage to be used.
- 8. Calculate the noise gain, noise gain = gain +  $\Delta V_{OLT}/V_{S}$ .
- 9. Set R<sub>F</sub>.
- 10. Calculate  $R_1$ ,  $R_1 = R_F/gain$ .
- 11. Calculate  $R_2$ ,  $R_2 = R_F/(\text{noise gain-gain})$ .
- 12. Calculate  $R_G$ ,  $R_G = R_F/(noise gain 1)$ .

Check that both the  $\rm V_{IN}$  and  $\rm V_{OUT}$  are within the voltage ranges of the LMH6618.

The following example is for a  $V_{\text{IN}}$  of 0V to 1V with a  $V_{\text{OUT}}$  of 2V to 4V.

- 1.  $V_{IN} = 0V \text{ to } 1V.$
- 2.  $V_{INMID} = 0V + (1V 0V)/2 = 0.5V$ .
- 3.  $V_{OUT} = 2V \text{ to } 4V.$
- 4.  $V_{OUTMID} = 2V + (4V 2V)/2 = 3V$ .
- 5. Gain = (4V 2V)/(1V 0V) = 2
- 6.  $\Delta V_{OUT} = 3V 2 \times 0.5V = 2$ .

- 7. For the example the supply voltage will be +5V.
- 8. Noise gain = 2 + 2/5V = 2.4.
- 9.  $R_F = 2 k\Omega$
- 10.  $R_1 = 2 k\Omega/2 = 1 k\Omega$
- 11.  $R_2 = 2 k\Omega/(2.4-2) = 5 k\Omega$ .
- 12.  $R_G = 2 k\Omega/(2.4 1) = 1.43 k\Omega$ .

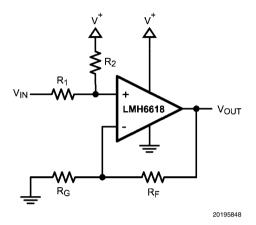


FIGURE 6. DC Level Shifting

#### 4th ORDER MULTIPLE FEEDBACK LOW-PASS FILTER

Figure 7 shows the LMH6618 used as the amplifier in a multiple feedback low-pass filter. This filter is set up to have a gain of +1 and a -3 dB point of 1 MHz. Values can be determined by using the WEBENCH® Active Filter Designer found at amplifiers.national.com.

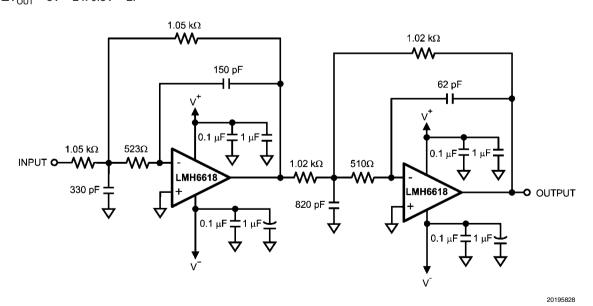
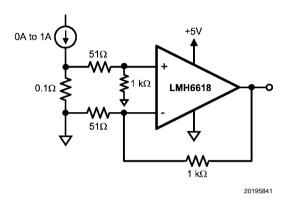


FIGURE 7. 4th Order Multiple Feedback Low-Pass Filter

#### **CURRENT SENSE AMPLIFIER**

With it's rail-to-rail input and output capability, low  $V_{OS}$ , and low  $I_B$  the LMH6618 is an ideal choice for a current sense amplifier application. *Figure 8* shows the schematic of the LMH6618 set up in a low-side sense configuration which provides a conversion gain of 2V/A. Voltage error due to  $V_{OS}$  can be calculated to be  $V_{OS}$  x  $(1 + R_F/R_G)$  or 0.6 mV x 21 = 12.6 mV. Voltage error due to  $I_O$  is  $I_O$  x  $I_F$  or 0.26  $I_O$  A x 1  $I_O$  = 0.26 mV. Hence total voltage error is 12.6 mV + 0.26 mV or 12.86 mV which translates into a current error of 12.86 mV/(2 V/A) = 6.43 mA.



**FIGURE 8. Current Sense Amplifier** 

#### TRANSIMPEDANCE AMPLIFIER

By definition, a photodiode produces either a current or voltage output from exposure to a light source. A Transimpedance Amplifier (TIA) is utilized to convert this low-level current to a usable voltage signal. The TIA often will need to be compensated to insure proper operation.

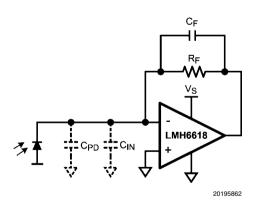


FIGURE 9. Photodiode Modeled with Capacitance Elements

Figure 9 shows the LMH6618 modeled with photodiode and the internal op amp capacitances. The LMH6618 allows circuit operation of a low intensity light due to its low input bias current by using larger values of gain (R<sub>F</sub>). The total capacitance (C<sub>T</sub>) on the inverting terminal of the op amp includes the photodiode capacitance (C<sub>PD</sub>) and the input capacitance of the op amp (C<sub>IN</sub>). This total capacitance (C<sub>T</sub>) plays an important role in the stability of the circuit. The noise gain of this circuit determines the stability and is defined by:

$$NG = \frac{1 + sR_F (C_T + C_F)}{1 + sC_F R_F}$$
 (1)

Where, 
$$f_Z \cong \frac{1}{2\pi R_F C_T}$$
 and  $f_P = \frac{1}{2\pi R_F C_F}$  (2)

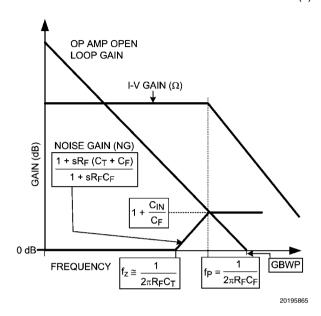


FIGURE 10. Bode Plot of Noise Gain Intersecting with Op Amp Open-Loop Gain

Figure 10 shows the bode plot of the noise gain intersecting the op amp open loop gain. With larger values of gain,  $C_T$  and  $R_F$  create a zero in the transfer function. At higher frequencies the circuit can become unstable due to excess phase shift around the loop.

A pole at  $f_P$  in the noise gain function is created by placing a feedback capacitor ( $C_F$ ) across  $R_F$ . The noise gain slope is flattened by choosing an appropriate value of  $C_F$  for optimum performance.

Theoretical expressions for calculating the optimum value of  $C_{\text{F}}$  and the expected -3 dB bandwidth are:

$$C_{F} = \sqrt{\frac{C_{T}}{2\pi R_{F}(GBWP)}}$$
(3)

$$f_{-3 dB} = \sqrt{\frac{GBWP}{2\pi R_F C_T}}$$
 (4)

Equation 4 indicates that the -3 dB bandwidth of the TIA is inversely proportional to the feedback resistor. Therefore, if the bandwidth is important then the best approach would be to have a moderate transimpedance gain stage followed by a broadband voltage gain stage.

Table 2 shows the measurement results of the LMH6618 with different photodiodes having various capacitances ( $C_{PD}$ ) and a feedback resistance ( $R_{E}$ ) of 1 kΩ.

TABLE 2. TIA (Figure 1) Compensation and Performance Results

C <sub>PD</sub>	C <sub>T</sub>	C <sub>F CAL</sub>	C <sub>F USED</sub>	f <sub>-3 dB CAL</sub>	f <sub>-3 dB MEAS</sub>	Peaking
(pF)	(pF)	(pF)	(pF)	(MHz)	(MHz)	(dB)
22	24	7.7	5.6	23.7	20	0.9
47	49	10.9	10	16.6	15.2	0.8
100	102	15.8	15	11.5	10.8	0.9
222	224	23.4	18	7.81	8	2.9

Note: GBWP = 65 MHz  $C_T = C_{PD} + C_{IN}$   $C_{IN} = 2 pF$  $V_S = \pm 2.5V$ 

Figure 11 shows the frequency response for the various photodiodes in *Table 2*.

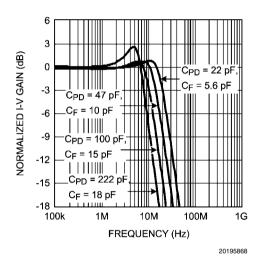
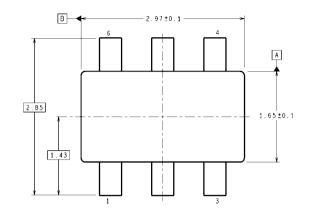
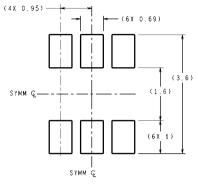


FIGURE 11. Frequency Response for Various Photodiode and Feedback Capacitors

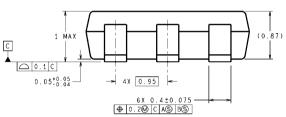
When analyzing the noise at the output of the TIA, it is important to note that the various noise sources (i.e. op amp noise voltage, feedback resistor thermal noise, input noise current, photodiode noise current) do not all operate over the same frequency band. Therefore, when the noise at the output is calculated, this should be taken into account. The op amp noise voltage will be gained up in the region between the noise gain's zero and pole (f<sub>Z</sub> and f<sub>P</sub> in Figure 10). The higher the values of R<sub>F</sub> and C<sub>T</sub>, the sooner the noise gain peaking starts and therefore its contribution to the total output noise will be larger. It is obvious to note that it is advantageous to minimize  $C_{\rm IN}$  by proper choice of op amp or by applying a reverse bias across the diode at the expense of excess dark current and noise.

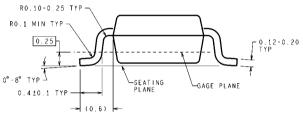
## Physical Dimensions inches (millimeters) unless otherwise noted





RECOMMENDED LAND PATTERN





DIMENSIONS ARE IN MILLIMETERS

MK06A (Rev D)

6-Pin TSOT23 NS Package Number MK06A

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